

L Number	Hits	Search Text	DB	Time stamp
79	22	((semiconductor substrate wafer silicon) and gate and (field adj plate)) and align\$8	EPO; JPO; DERWENT; IBM_TDB	2004/11/04 10:20
80	0	gate and (field adj plate) and (tiwn (titanium adj tungsten adj nitride) (tungsten adj titanium adj nitride))	EPO; JPO; DERWENT; IBM_TDB	2004/11/04 11:03
81	34	(gate (field adj plate)) and (tiwn (titanium adj tungsten adj nitride) (tungsten adj titanium adj nitride))	EPO; JPO; DERWENT; IBM_TDB	2004/11/04 11:04
82	1	(semiconductor substrate wafer silicon) and (gate same (field adj plate) same (tiwn (titanium adj tungsten adj nitride) (tungsten adj titanium adj nitride)))	USPAT; US-PGPUB	2004/11/04 11:49
83	2755	438/182.ccls. 438/270.ccls. 438/294.ccls. 438/299.ccls. 438/454.ccls. 438/586.ccls. 438/589.ccls.	USPAT; US-PGPUB	2004/11/04 12:12
84	68	(438/182.ccls. 438/270.ccls. 438/294.ccls. 438/299.ccls. 438/454.ccls. 438/586.ccls. 438/589.ccls.) and (gate same (field adj plate))	USPAT; US-PGPUB	2004/11/04 12:13
-	2	5831320.pn. 6033948.pn.	USPAT; US-PGPUB	2004/11/03 16:35
-	1003	(semiconductor substrate wafer silicon) and (gate same (field adj plate))	USPAT; US-PGPUB	2004/11/04 12:12
-	98	(semiconductor substrate wafer silicon) and (gate same (field adj plate) same align\$8 same (insulat\$8 dielectric oxide dioxide nitride))	USPAT; US-PGPUB	2004/11/03 16:41
-	311	(semiconductor substrate wafer silicon) and gate and (field adj plate)	EPO; JPO; DERWENT; IBM_TDB	2004/11/04 10:59
-	249	(semiconductor substrate wafer silicon) and (gate same (field adj plate))	EPO; JPO; DERWENT; IBM_TDB	2004/11/03 16:43
-	268	((semiconductor substrate wafer silicon) and gate and (field adj plate)) and (insulat\$8 dielectric oxide dioxide nitride)	EPO; JPO; DERWENT; IBM_TDB	2004/11/03 16:41
-	172	(semiconductor substrate wafer silicon) and (gate with (field adj plate))	EPO; JPO; DERWENT; IBM_TDB	2004/11/03 16:43
-	116	(semiconductor substrate wafer silicon) and (gate same (field adj plate) same align\$8)	USPAT; US-PGPUB	2004/11/04 12:09